

Features

- Center amplifying gate
- Metal case with ceramic insulator
- Low on-state and switching losses

I_{T(AV)} **1640A**
V_{DRM/V_{RRM}} **3100~4200V**

Typical Applications

- AC controllers
- DC and AC motor control
- Controlled rectifiers

I_{TSM} **20 kA**
I²t **2000 10³A²s**



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _J (°C)	VALUE			UNIT
				Min	Type	Max	
I _{T(AV)}	Mean on-state current	180° half sine wave 50Hz Double side cooled,	125			1640	A
V _{DRM} V _{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	tp=10ms	125	3100		4200	V
I _{DRM} I _{RRM}	Repetitive peak current	at V _{DRM} at V _{RRM}	125			120	mA
I _{TSM}	Surge on-state current	10ms half sine wave	125			20	kA
I ² t	I ² t for fusing coordination	V _R =0.6V _{RRM}				2000	A ² s*10 ³
V _{TO}	Threshold voltage		125			1.17	V
r _T	On-state slope resistance					0.35	mΩ
V _{TM}	Peak on-state voltage	I _{TM} =3000A, F=32kN	25			2.60	V
dv/dt	Critical rate of rise of off-state voltage	V _{DM} =0.67V _{DRM}	125			1000	V/μs
di/dt	Critical rate of rise of on-state current	V _{DM} = 67%V _{DRM} Gate source I _{GM} =1.5A, di/dt=1A/μs, t _r ≤0.5μs, t _{p(I_{GON})} ≥30μs	125			200	A/μs
Q _{rr}	Recovery charge	I _{TM} =2000A, tp=2000μs, di/dt=-20A/μs, V _R =50V	125		2000		μC
I _{GT}	Gate trigger current	V _A =12V, I _A =1A	25	40		300	mA
V _{GT}	Gate trigger voltage			0.8		3.0	V
I _H	Holding current			20		300	mA
V _{GD}	Non-trigger gate voltage	V _{DM} =67%V _{DRM}	125	0.3			V
R _{th(j-c)}	Thermal resistance Junction to case	DC, double side cooled Clamping force 32kN				0.0130	°C /W
R _{th(c-h)}	Thermal resistance case to heatsink					0.0035	
F _m	Mounting force			27		34	kN
T _{stg}	Stored temperature			-40		140	°C
W _t	Weight				820		g
Outline		P68					

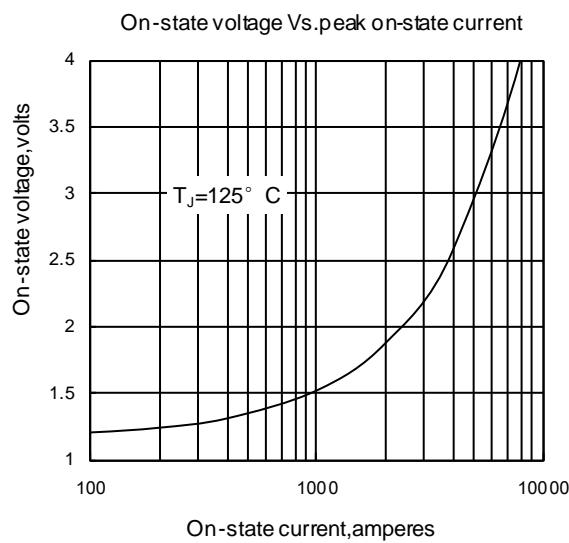


Fig1

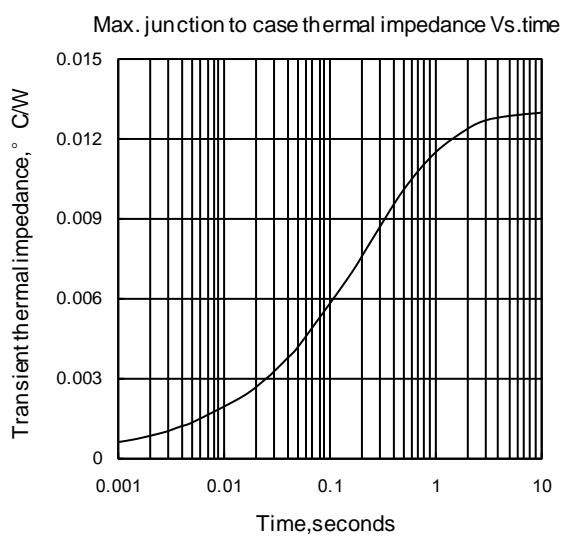


Fig2

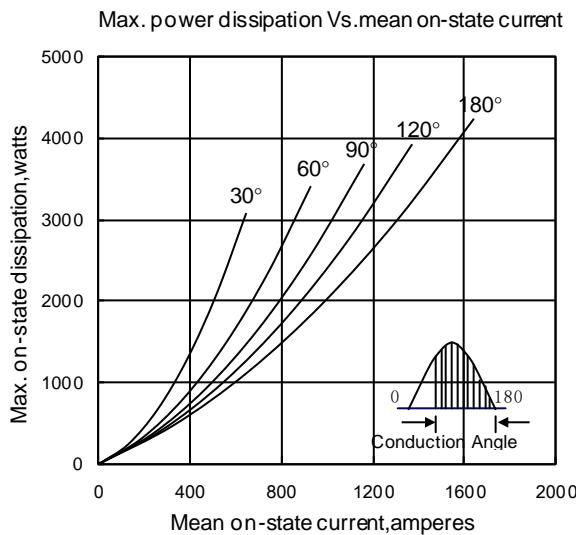


Fig3

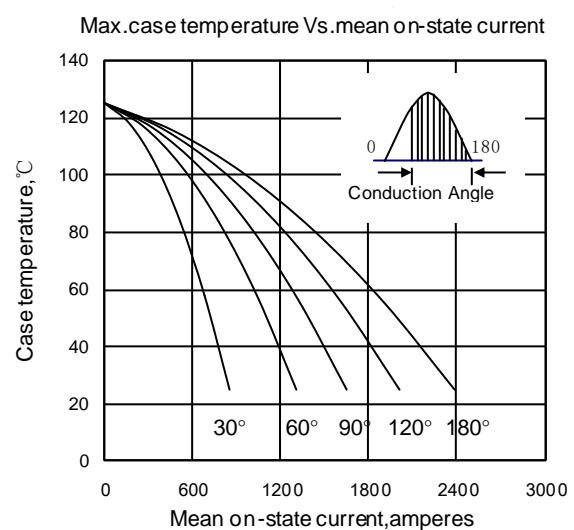


Fig4

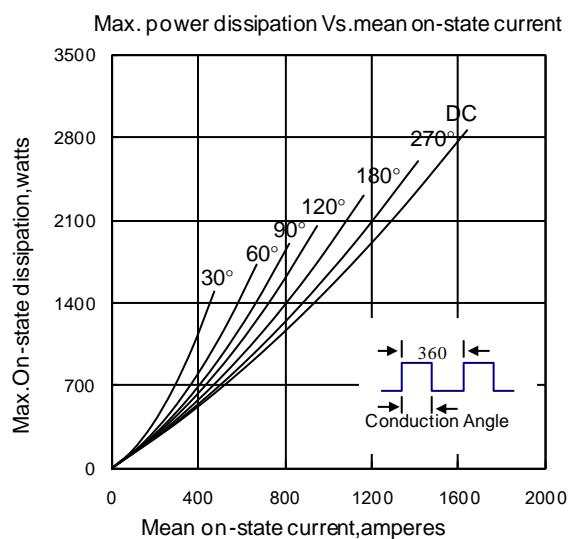


Fig5

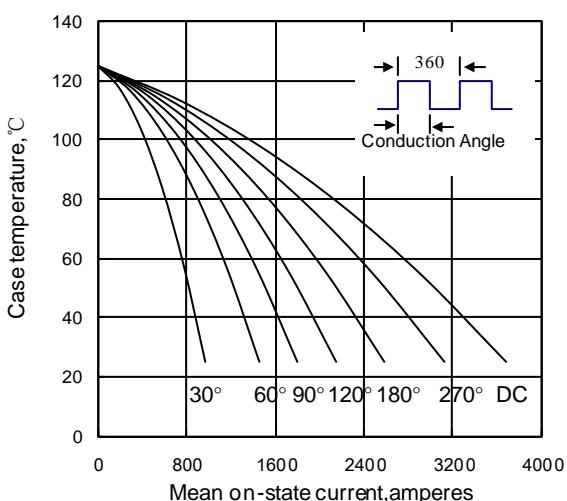


Fig6

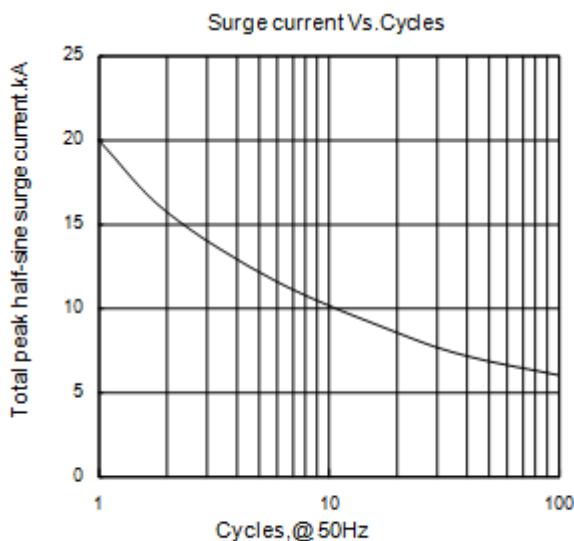


Fig 7

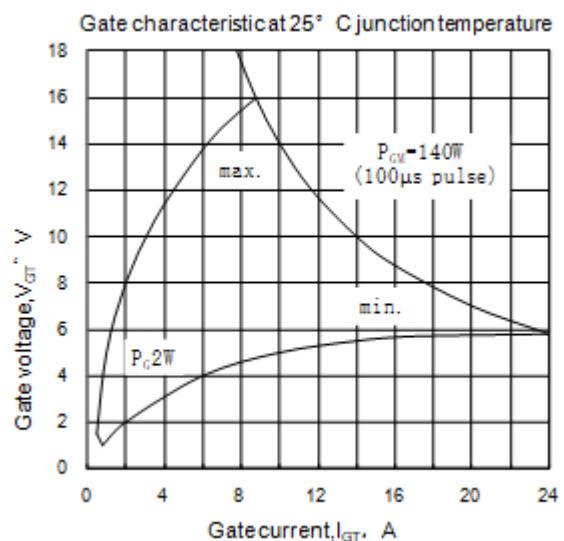


Fig 8

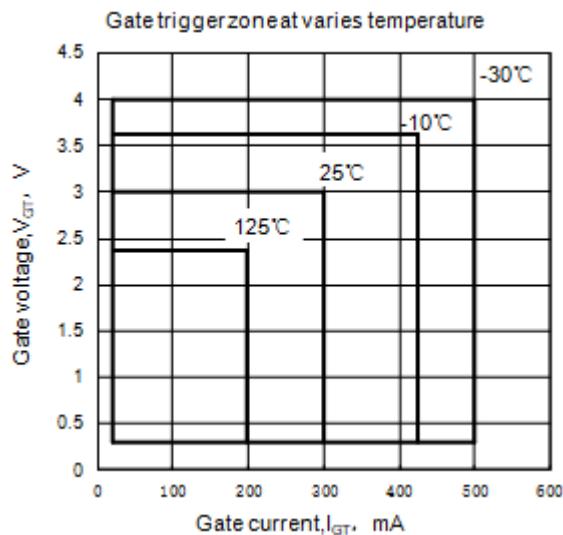


Fig 9

